**FUJITSU SEMICONDUCTOR
DATA SHEET**

MEMORY
CMOS
4 M × 4 BIT
HYPER PAGE MODE DYNAMIC RAM

MB81V17405A-60/-70

CMOS 4,194,304 × 4 BIT Hyper Page Mode Dynamic RAM

■ DESCRIPTION

The Fujitsu MB81V17405A is a fully decoded CMOS Dynamic RAM (DRAM) that contains 16,777,216 memory cells accessible in 4-bit increments. The MB81V17405A features a "hyper page" mode of operation whereby high-speed random access of up to 2,048 × 4 bits of data within the same row can be selected. The MB81V17405A DRAM is ideally suited for mainframe, buffers, hand-held computers video imaging equipment, and other memory applications where very low power dissipation and high bandwidth are basic requirements of the design. Since the standby current of the MB81V17405A is very small, the device can be used as a non-volatile memory in equipment that uses batteries for primary and/or auxiliary power.

The MB81V17405A is fabricated using silicon gate CMOS and Fujitsu's advanced four-layer polysilicon and two-layer aluminum process. This process, coupled with advanced stacked capacitor memory cells, reduces the possibility of soft errors and extends the time interval between memory refreshes. Clock timing requirements for the MB81V17405A are not critical and all inputs are LVTTL compatible.

■ PRODUCT LINE & FEATURES

Parameter		MB81V17405A-60	MB81V17405A-70
$\overline{RAS}$ Access Time		60 ns max.	70 ns max.
Random Cycle Time		104 ns min.	124 ns min.
Address Access Time		30 ns max.	35 ns max.
$\overline{CAS}$ Access Time		15 ns max.	17 ns max.
Hyper Page Mode Cycle Time		25 ns min.	30 ns min.
Low Power Dissipation	Operating Current	396 mW max.	342 mW max.
	Standby Current	7.2 mW max. (LVTTL level)/3.6 mW max. (CMOS level)	

- 4,194,304 words × 4 bit organization
- Silicon gate, CMOS, Advanced stacked Capacitor Cell
- All input and output are LVTTL compatible
- 2048 refresh cycles every 32.8 ms
- Early write or $\overline{OE}$ controlled write capability
- $\overline{RAS}$-only, $\overline{CAS}$-before-$\overline{RAS}$, or Hidden Refresh
- Hyper Page Mode, Read-Modify-Write capability
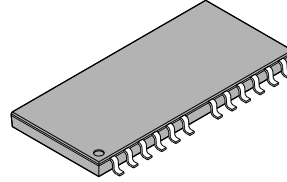- On chip substrate bias generator for high performance

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■ PACKAGE

Plastic SOJ Package
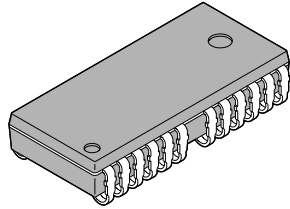
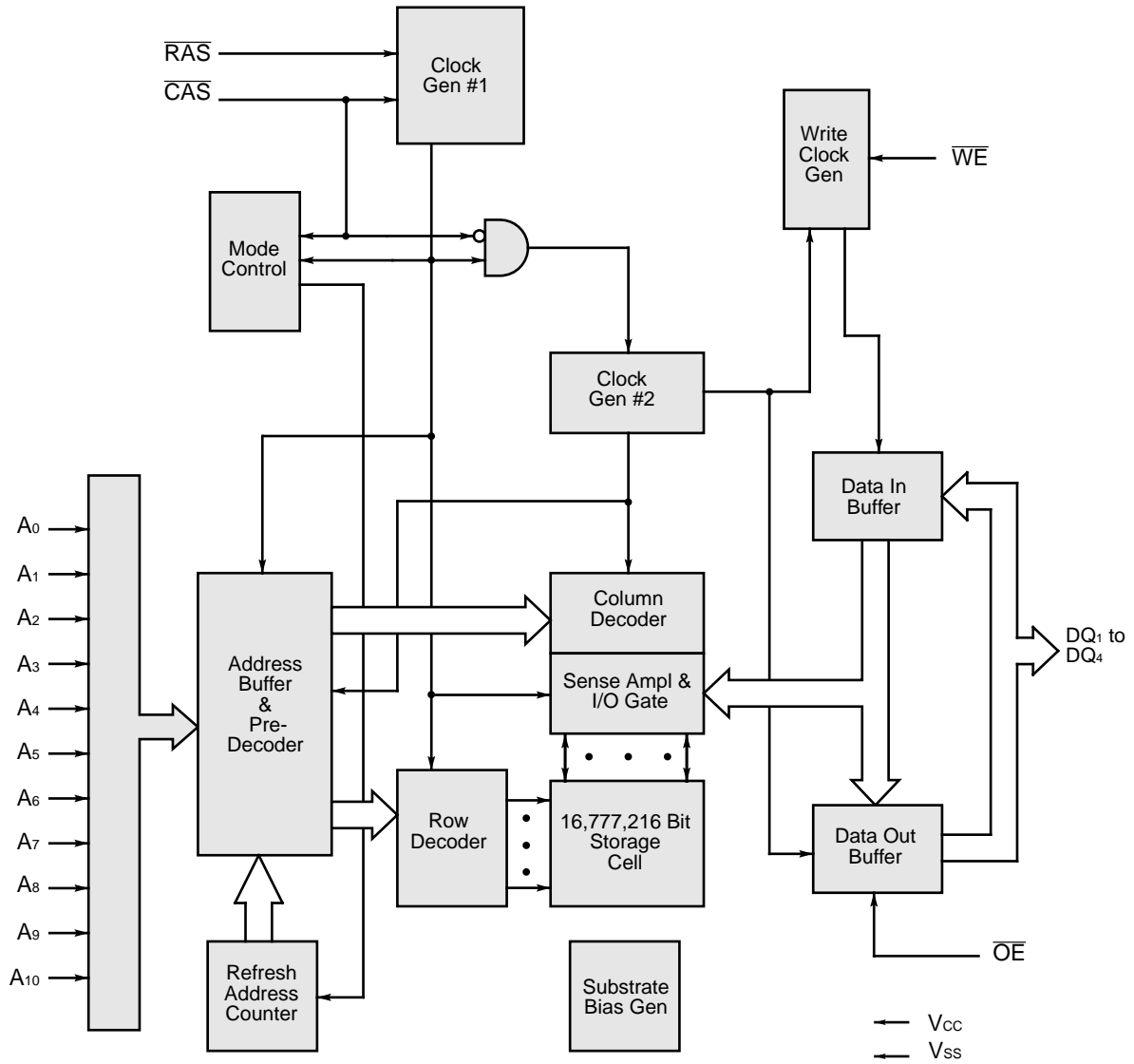Plastic TSOP (II) Package

(LCC-26P-M09)

(FPT-26P-M05)
(Normal Bend)

Package and Ordering Information

– 26-pin plastic (300 mil) SOJ, order as MB81V17405A-××PJ
– 26-pin plastic (300 mil) TSOP-II with normal bend leads, order as MB81V17405A-××PFTN
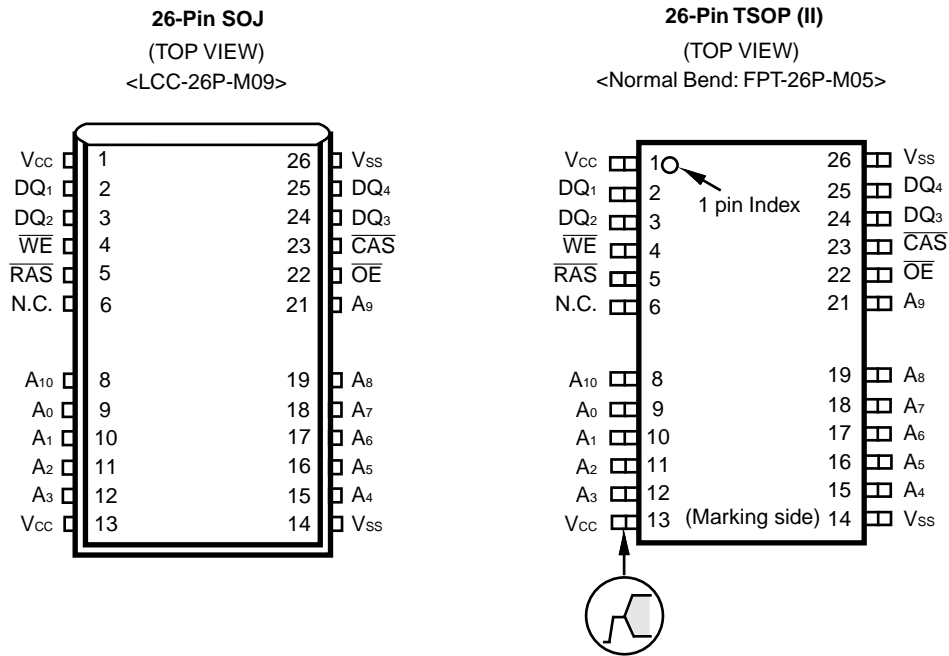
Fig. 1 – MB81V17405A DYNAMIC RAM - BLOCK DIAGRAM

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■ PIN ASSIGNMENTS AND DESCRIPTIONS

26-Pin SOJ
(TOP VIEW)
<LCC-26P-M09>

V_{CC}	1	26	V_{SS}
DQ_1	2	25	DQ_4
DQ_2	3	24	DQ_3
$\overline{WE}$	4	23	$\overline{CAS}$
$\overline{RAS}$	5	22	$\overline{OE}$
N.C.	6	21	A_9
A_{10}	8	19	A_8
A_0	9	18	A_7
A_1	10	17	A_6
A_2	11	16	A_5
A_3	12	15	A_4
V_{CC}	13	14	V_{SS}

26-Pin TSOP (II)
(TOP VIEW)
<Normal Bend: FPT-26P-M05>

1 pin Index

(Marking side)

V_{CC}	1	26	V_{SS}
DQ_1	2	25	DQ_4
DQ_2	3	24	DQ_3
$\overline{WE}$	4	23	$\overline{CAS}$
$\overline{RAS}$	5	22	$\overline{OE}$
N.C.	6	21	A_9
A_{10}	8	19	A_8
A_0	9	18	A_7
A_1	10	17	A_6
A_2	11	16	A_5
A_3	12	15	A_4
V_{CC}	13	14	V_{SS}

Designator	Function
DQ_1 to DQ_4	Data Input/ Output
$\overline{WE}$	Write Enable
$\overline{RAS}$	Row address strobe
A_0 to A_{10}	Address inputs
V_{CC}	+3.3 volt power supply
$\overline{OE}$	Output enable
$\overline{CAS}$	Column address strobe
V_{SS}	Circuit ground
N.C.	No Connection

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■ FUNCTIONAL TRUTH TABLE

Operation Mode	Clock Input				Address Input		Input Data		Refresh	Note
	$\overline{RAS}$	$\overline{CAS}$	$\overline{WE}$	$\overline{OE}$	Row	Column	Input	Output		
Standby	H	H	X	X	—	—	—	High-Z	—	
Read Cycle	L	L	H	L	Valid	Valid	—	Valid	Yes*	$t_{RCS} \geq t_{RCS}$ (min)
Write Cycle (Early Write)	L	L	L	X	Valid	Valid	Valid	High-Z	Yes*	$t_{WCS} \geq t_{WCS}$ (min)
Read-Modify-Write Cycle	L	L	H→L	L→H	Valid	Valid	Valid	Valid	Yes*	
$\overline{RAS}$-only Refresh Cycle	L	H	X	X	Valid	—	—	High-Z	Yes	
$\overline{CAS}$-before-$\overline{RAS}$ Refresh Cycle	L	L	H	X	—	—	—	High-Z	Yes	$t_{CSR} \geq t_{CSR}$ (min)
Hidden Refresh Cycle	H→L	L	H→X	L	—	—	—	Valid	Yes	Previous data is kept.

X: "H" or "L"
* : It is impossible in Hyper Page Mode.

■ FUNCTIONAL OPERATION

ADDRESS INPUTS

Twenty-two input bits are required to decode any four of 16,777,216 cell addresses in the memory matrix. Since only twelve address bits (A0 to A10) are available, the row and column inputs are separately strobed by $\overline{RAS}$ and $\overline{CAS}$ as shown in Figure 1. First, twelve row address bits are input on pins A_0-through-A_{10} and latched with the row address strobe ($\overline{RAS}$) then, ten column address bits are input and latched with the column address strobe ($\overline{CAS}$). Both row and column addresses must be stable on or before the falling edge of $\overline{RAS}$ and $\overline{CAS}$, respectively. The address latches are of the flow-through type; thus, address information appearing after t_{RAH} (min)+ t_T is automatically treated as the column address.

WRITE ENABLE

The read or write mode is determined by the logic state of $\overline{WE}$. When $\overline{WE}$ is active Low, a write cycle is initiated; when $\overline{WE}$ is High, a read cycle is selected. During the read mode, input data is ignored.

DATA INPUTS

Input data is written into memory in either of three basic ways : an early write cycle, an $\overline{OE}$ (delayed) write cycle, and a read-modify-write cycle. The falling edge of $\overline{WE}$ or $\overline{CAS}$, whichever is later, serves as the input data-latch strobe. In an early write cycle, the input data (DQ_1 to DQ_4) is strobed by $\overline{CAS}$ and the setup/hold times are referenced to $\overline{CAS}$ because $\overline{WE}$ goes Low before $\overline{CAS}$. In a delayed write or a read-modify-write cycle, $\overline{WE}$ goes Low after $\overline{CAS}$; thus, input data is strobed by $\overline{WE}$ and all setup/hold times are referenced to the write-enable signal.

DATA OUTPUTS

The three-state buffers are LVTTL compatible with a fanout of one TTL load. Polarity of the output data is identical to that of the input; the output buffers remain in the high-impedance state until the column address strobe goes Low. When a read or read-modify-write cycle is executed, valid outputs and High-Z state are obtained under the following conditions:

t_{RAC} : from the falling edge of $\overline{RAS}$ when t_{RCD} (max) is satisfied.
t_{CAC} : from the falling edge of $\overline{CAS}$ when t_{RCD} is greater than t_{RCD} (max).

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t_{AA} : from column address input when t_{RAD} is greater than t_{RAD} (max), and t_{RCD} (max) is satisfied.

t_{OEA} : from the falling edge of $\overline{OE}$ when $\overline{OE}$ is brought Low after t_{RAC}, t_{CAC}, or t_{AA}.

t_{OEZ} : from $\overline{OE}$ inactive.

t_{OFF} : from $\overline{CAS}$ inactive while $\overline{RAS}$ inactive.

t_{OFR} : from $\overline{RAS}$ inactive while $\overline{CAS}$ inactive.

t_{WEZ} : from $\overline{WE}$ active while $\overline{CAS}$ inactive.

The data remains valid after either $\overline{OE}$ is inactive, or both $\overline{RAS}$ and $\overline{CAS}$ are inactive, or $\overline{CAS}$ is reactived. When an early write is execute, the output buffers remain in a high-impedance state during the entire cycle.

HYPER PAGE MODE OPERATION

The hyper page mode of operation provides faster memory access and lower power dissipation. The hyper page mode is implemented by keeping the same row address and strobing in successive column addresses. To satisfy these conditions, $\overline{RAS}$ is held Low for all contiguous memory cycles in which row addresses are common. For each page of memory (with column address locations), any of $2{,}048 \times 4$ bits can be accessed and, when multiple MB81V17405As are used, $\overline{CAS}$ is decoded to select the desired memory page. Hyper page mode operations need not be addressed sequentially and combinations of read, write, and/or read-modify-write cycles are permitted. Hyper page mode features that output remains valid when $\overline{CAS}$ is inactive until $\overline{CAS}$ is reactivated.

■ ABSOLUTE MAXIMUM RATINGS (See WARNING)

Parameter	Symbol	Value	Unit
Voltage at Any Pin Relative to V_{SS}	V_{IN}, V_{OUT}	−0.5 to +4.6	V
Voltage of V_{CC} Supply Relative to V_{SS}	V_{CC}	−0.5 to +4.6	V
Power Dissipation	P_D	1.0	W
Short Circuit Output Current	I_{OUT}	−50 to +50	mA
Operating Temperature	T_{OPE}	0 to +70	°C
Storage Temperature	T_{STG}	−55 to +125	°C

WARNING: Semiconductor devices can be permanently damaged by application of stress (voltage, current, temperature, etc.) in excess of absolute maximum ratings. Do not exceed these ratings.

■ RECOMMENDED OPERATING CONDITIONS

Parameter	Notes	Symbol	Min.	Typ.	Max.	Unit	Ambient Operating Temp.
Supply Voltage	*1	V_{CC}	3.0	3.3	3.6	V	0°C to +70°C
		V_{SS}	0	0	0		
Input High Voltage, All Inputs	*1	V_{IH}	2.0	—	V_{CC}+0.3 V	V	
Input Low Voltage, All Inputs*	*1	V_{IL}	−0.3	—	0.8	V	

* : Undershoots of up to −1.2 volts with a pulse width not exceeding 20 ns are acceptable.

WARNING: Recommended operating conditions are normal operating ranges for the semiconductor device. All the device's electrical characteristics are warranted when operated within these ranges.

Always use semiconductor devices within the recommended operating conditions. Operation outside these ranges may adversely affect reliability and could result in device failure.

No warranty is made with respect to uses , operating conditions, or combinations not represented on the data sheet. Users considering application outside the listed conditions are advised to contact their FUJITSU representative beforehand.

■ CAPACITANCE

$(T_A = 25°C, f = 1 MHz)$

Parameter	Symbol	Typ.	Max.	Unit
Input Capacitance, A_0 to A_{10}	C_{IN1}	—	5	pF
Input Capacitance, $\overline{RAS}$, $\overline{CAS}$, $\overline{WE}$, $\overline{OE}$	C_{IN2}	—	5	pF
Input/Output Capacitance, DQ_1 to DQ_4	C_{DQ}	—	7	pF

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■ DC CHARACTERISTICS
(At recommended operating conditions unless otherwise noted.)   Note 3

Parameter Notes		Symbol	Condition	Value			Unit
				Min.	Typ.	Max.	
Output High Voltage *1		I_{OH}	$I_{OH} = -2$ mA	2.4	—	—	V
Output Low Voltage *1		I_{OL}	$I_{OL} = 2$ mA	—	—	0.4	
Input Leakage Current (Any Input)		$I_{I(L)}$	0 V ≤ V_{IN} ≤ 3.6 V; 3.0 V ≤ V_{CC} ≤ 3.6 V V_{SS} = 0 V; All other pins not under test = 0 V	−10	—	10	μA
Output Leakage Current		$I_{O(L)}$	0 V ≤ V_{OUT} ≤ 3.6 V; Data out disabled	−10	—	10	
Operating Current (Average Power Supply Current) *2	MB81V17405A-60	I_{CC1}	$\overline{RAS}$ & $\overline{CAS}$ cycling; t_{RC} = min	—	—	110	mA
	MB81V17405A-70					95	
Standby Current (Power Supply Current)	LVTTL Level	I_{CC2}	$\overline{RAS} = \overline{CAS} = V_{IH}$	—	—	2.0	mA
	CMOS Level		$\overline{RAS} = \overline{CAS} \geq V_{CC} -0.2$ V			1.0	
Refresh Current #1 (Average Power Supply Current) *2	MB81V17405A-60	I_{CC3}	$\overline{CAS} = V_{IH}$, $\overline{RAS}$ cycling; t_{RC} = min	—	—	110	mA
	MB81V17405A-70					95	
Hyper Page Mode Current *2	MB81V17405A-60	I_{CC4}	$\overline{RAS} = V_{IL,}$ $\overline{CAS}$ cycling; t_{HPC} = min	—	—	90	mA
	MB81V17405A-70					80	
Refresh Current #2 (Average Power Supply Current) *2	MB81V17405A-60	I_{CC5}	$\overline{RAS}$ cycling; $\overline{CAS}$-before-$\overline{RAS}$; t_{RC} = min	—	—	110	mA
	MB81V17405A-70					95	

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■ AC CHARACTERISTICS
(At recommended operating conditions unless otherwise noted.)   Notes 3, 4, 5

No.	Parameter	Notes	Symbol	MB81V17405A-60		MB81V17405A-70		Unit
				Min.	Max.	Min.	Max.	
1	Time Between Refresh		t_{REF}	—	32.8	—	32.8	ms
2	Random Read/Write Cycle Time		t_{RC}	104	—	124	—	ns
3	Read-Modify-Write Cycle Time		t_{RWC}	138	—	162	—	ns
4	Access Time from $\overline{RAS}$	*6,9	t_{RAC}	—	60	—	70	ns
5	Access Time from $\overline{CAS}$	*7,9	t_{CAC}	—	15	—	17	ns
6	Column Address Access Time	*8,9	t_{AA}	—	30	—	35	ns
7	Output Hold Time		t_{OH}	3	—	3	—	ns
8	Output Hold Time from $\overline{CAS}$		t_{OHC}	5	—	5	—	ns
9	Output Buffer Turn On Delay Time		t_{ON}	0	—	0	—	ns
10	Output Buffer Turn Off Delay Time	*10	t_{OFF}	—	15	—	17	ns
11	Output Buffer Turn Off Delay Time from $\overline{RAS}$	*10	t_{OFR}	—	15	—	17	ns
12	Output Buffer Turn Off Delay Time from $\overline{WE}$	*10	t_{WEZ}	—	15	—	17	ns
13	Transition Time		t_{T}	1	50	1	50	ns
14	$\overline{RAS}$ Precharge Time		t_{RP}	40	—	50	—	ns
15	$\overline{RAS}$ Pulse Width		t_{RAS}	60	100000	70	100000	ns
16	$\overline{RAS}$ Hold Time		t_{RSH}	15	—	17	—	ns
17	$\overline{CAS}$ to $\overline{RAS}$ Precharge Time	*21	t_{CRP}	5	—	5	—	ns
18	$\overline{RAS}$ to $\overline{CAS}$ Delay Time	*11,12,22	t_{RCD}	14	45	14	53	ns
19	$\overline{CAS}$ Pulse Width		t_{CAS}	10	—	13	—	ns
20	$\overline{CAS}$ Hold Time		t_{CSH}	40	—	50	—	ns
21	$\overline{CAS}$ Precharge Time (Normal)	*19	t_{CPN}	10	—	10	—	ns
22	Row Address Set Up Time		t_{ASR}	0	—	0	—	ns
23	Row Address Hold Time		t_{RAH}	10	—	10	—	ns
24	Column Address Set Up Time		t_{ASC}	0	—	0	—	ns
25	Column Address Hold Time		t_{CAH}	10	—	10	—	ns
26	Column Address Hold Time from $\overline{RAS}$		t_{AR}	24	—	24	—	ns
27	$\overline{RAS}$ to Column Address Delay Time	*13	t_{RAD}	12	30	12	35	ns
28	Column Address to $\overline{RAS}$ Lead Time		t_{RAL}	30	—	35	—	ns
29	Column Address to $\overline{CAS}$ Lead Time		t_{CAL}	23	—	28	—	ns
30	Read Command Set Up Time		t_{RCS}	0	—	0	—	ns

(Continued)

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No.	Parameter	Notes	Symbol	MB81V17405A-60		MB81V17405A-70		Unit
				Min.	Max.	Min.	Max.	
31	Read Command Hold Time Referenced to $\overline{RAS}$	*14	t$_{RRH}$	0	—	0	—	ns
32	Read Command Hold Time Referenced to $\overline{CAS}$	*14	t$_{RCH}$	0	—	0	—	ns
33	Write Command Set Up Time	*15,20	t$_{WCS}$	0	—	0	—	ns
34	Write Command Hold Time		t$_{WCH}$	10	—	10	—	ns
35	Write Hold Time from $\overline{RAS}$		t$_{WCR}$	24	—	24	—	ns
36	$\overline{WE}$ Pulse Width		t$_{WP}$	10	—	10	—	ns
37	Write Command to $\overline{RAS}$ Lead Time		t$_{RWL}$	15	—	17	—	ns
38	Write Command to $\overline{CAS}$ Lead Time		t$_{CWL}$	10	—	13	—	ns
39	DIN Set Up Time		t$_{DS}$	0	—	0	—	ns
40	DIN Hold Time		t$_{DH}$	10	—	10	—	ns
41	Data Hold Time from $\overline{RAS}$		t$_{DHR}$	24	—	24	—	ns
42	$\overline{RAS}$ to $\overline{WE}$ Delay Time	*20	t$_{RWD}$	77	—	89	—	ns
43	$\overline{CAS}$ to $\overline{WE}$ Delay Time	*20	t$_{CWD}$	32	—	36	—	ns
44	Column Address to $\overline{WE}$ Delay Time	*20	t$_{AWD}$	47	—	54	—	ns
45	$\overline{RAS}$ Precharge Time to $\overline{CAS}$ Active Time (Refresh Cycles)		t$_{RPC}$	5	—	5	—	ns
46	$\overline{CAS}$ Set Up Time for $\overline{CAS}$-before-$\overline{RAS}$ Refresh		t$_{CSR}$	0	—	0	—	ns
47	$\overline{CAS}$ Hold Time for $\overline{CAS}$-before-$\overline{RAS}$ Refresh		t$_{CHR}$	10	—	12	—	ns
48	Access Time from $\overline{OE}$	*9	t$_{OEA}$	—	15	—	17	ns
49	Output Buffer Turn Off Delay from $\overline{OE}$	*10	t$_{OEZ}$	—	15	—	17	ns
50	$\overline{OE}$ to $\overline{RAS}$ Lead Time for Valid Data		t$_{OEL}$	10	—	10	—	ns
51	$\overline{OE}$ to $\overline{CAS}$ Lead Time		t$_{COL}$	5	—	5	—	ns
52	$\overline{OE}$ Hold Time Referenced to $\overline{WE}$	*16	t$_{OEH}$	5	—	5	—	ns
53	$\overline{OE}$ to Data in Delay Time		t$_{OED}$	15	—	17	—	ns
54	$\overline{RAS}$ to Data in Delay Time		t$_{RDD}$	15	—	17	—	ns
55	$\overline{CAS}$ to Data in Delay Time		t$_{CDD}$	15	—	17	—	ns
56	DIN to $\overline{CAS}$ Delay Time	*17	t$_{DZC}$	0	—	0	—	ns
57	DIN to $\overline{OE}$ Delay Time	*17	t$_{DZO}$	0	—	0	—	ns
58	$\overline{OE}$ Precharge Time		t$_{OEP}$	8	—	8	—	ns
59	$\overline{OE}$ Hold Time Referenced to $\overline{CAS}$		t$_{OECH}$	10	—	10	—	ns

(Continued)

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(Continued)

No.	Parameter	Notes	Symbol	MB81V17405A-60		MB81V17405A-70		Unit
				Min.	Max.	Min.	Max.	
60	$\overline{WE}$ Precharge Time		t_{WPZ}	8	—	8	—	ns
61	$\overline{WE}$ to Date in Delay Time		t_{WED}	15	—	17	—	ns
62	Hyper Page Mode $\overline{RAS}$ Pulse Width		t_{RASP}	—	100000	—	100000	ns
63	Hyper Page Mode Read/Write Cycle Time		t_{HPC}	25	—	30	—	ns
64	Hyper Page Mode Read-Modify-Write Cycle Time		t_{HPRWC}	69	—	79	—	ns
65	Access Time from $\overline{CAS}$ Precharge	*9,18	t_{CPA}	—	35	—	40	ns
66	Hyper Page Mode $\overline{CAS}$ Precharge Time		t_{CP}	10	—	10	—	ns
67	Hyper Page Mode $\overline{RAS}$ Hold Time from $\overline{CAS}$ Precharge		t_{RHCP}	35	—	40	—	ns
68	Hyper Page Mode $\overline{CAS}$ Precharge to $\overline{WE}$ Delay Time		t_{CPWD}	52	—	59	—	ns

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Notes: *1. Referenced to V_{SS}.

*2. I_{CC} depends on the output load conditions and cycle rates; The specified values are obtained with the output open. I_{CC} depends on the number of address change as $\overline{RAS} = V_{IL}$, $\overline{CAS} = V_{IH}$ and $V_{IL} > -0.3$ V. I_{CC1}, I_{CC3} and I_{CC5} are specified at one time of address change during $\overline{RAS} = V_{IL}$ and $\overline{CAS} = V_{IH}$. I_{CC2} is specified during $\overline{RAS} = V_{IH}$ and $V_{IL} > -0.3$ V. I_{CC4} is specified assuming that all column addresses change only one time during each hyper page mode cycle.

*3. An initial pause ($\overline{RAS} = \overline{CAS} = V_{IH}$) of 200 μs is required after power-up followed by any eight $\overline{RAS}$-only cycles before proper device operation is achieved. In case of using internal refresh counter, a minimum of eight $\overline{CAS}$-before-$\overline{RAS}$ initialization cycles instead of 8 $\overline{RAS}$ cycles are required.

*4. AC characteristics assume $t_T = 2$ ns.

*5. Input voltage levels are 0 V and 3.0 V, and input reference levels are V_{IH} (min) and V_{IL} (max) for measuring timing of input signals. Also, the transition time (t_T) is measured between V_{IH} (min) and V_{IL} (max). The output reference levels are $V_{OH} = 2.0$ V and $V_{OL} = 0.8$ V.

*6. Assumes that $t_{RCD} \leq t_{RCD}$ (max), $t_{RAD} \leq t_{RAD}$ (max). If t_{RCD} is greater than the maximum recommended value shown in this table, t_{RAD} will be increased by the amount that t_{RCD} exceeds the value shown. Refer to Fig. 2 and 3.

*7. If $t_{RCD} \geq t_{RCD}$ (max), $t_{RAD} \geq t_{RAD}$ (max), and $t_{ASC} \geq t_{AA}$ - t_{CAC} - t_T access time is t_{CAC}.

*8. If $t_{RAD} \geq t_{RAD}$ (max) and $t_{ASC} \geq t_{AA}$ - t_{CAC} - t_T, access time is t_{AA}.

*9. Measured with a load equivalent to one TTL load and 100 pF.

*10. t_{OFF} and t_{OEZ} is specified that output buffer change to high-impedance state.

*11. Operation within the t_{RCD} (max) limit ensures that t_{RAC} (max) can be met. t_{RCD} (max) is specified as a reference point only; if t_{RCD} is greater than the specified t_{RCD} (max) limit, access time is controlled exclusively by t_{CAC} or t_{AA}.

*12. t_{RCD} (min) = t_{RAH} (min) + $2t_T$ + t_{ASD} (min).

*13. Operation within the t_{RAD} (max) limit ensures that t_{RAC} (max) can be met. t_{RAD} (max) is specified as a reference point only; if t_{RAD} is greater than the specified t_{RAD} (max) limit, access time is controlled exclusively by t_{CAC} or t_{AA}.

*14. Either t_{RRH} or t_{RCH} must be satisfied for a read cycle.

*15. t_{WCS} is specified as a reference point only. If $t_{WCS} \geq t_{WCS}$ (min) the data output pin will remain High-Z state through entire cycle.

*16. Assumes that $t_{WCS} < t_{WCS}$ (min).

*17. Either t_{DZC} or t_{DZO} must be satisfied.

*18. t_{CPA} is access time from the selection of a new column address (that is caused by changing $\overline{CAS}$ from "L" to "H"). Therefore, if t_{CP} is long, t_{CPA} is longer than t_{CPA} (max).

*19. Assumes that $\overline{CAS}$-before-$\overline{RAS}$ refresh.

*20. t_{WCS}, t_{CWD}, t_{RWD} and t_{AWD} are not restrictive operating parameters. They are included in the data sheet as an electrical characteristic only. If $t_{WCS} > t_{WCS}$ (min), the cycle is an early write cycle and D_{OUT} pin will maintain high-impedance state thoughout the entire cycle. If $t_{CWD} > t_{CWD}$ (min), $t_{RWD} > t_{RWD}$ (min), and $t_{AWD} > t_{AWD}$ (min), the cycle is a read-modify-write cycle and data from the selected cell will appear at the D_{OUT} pin. If neither of the above conditions is satisfied, the cycle is a delayed write cycle and invalid data will appear the D_{OUT} pin, and write operation can be executed by satisfying t_{RWL}, t_{CWL}, and t_{RAL} specifications.

*21. The last $\overline{CAS}$ rising edge.

*22. The first $\overline{CAS}$ falling edge.

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Fig. 2 – t_{RAC} vs. t_{RCD}
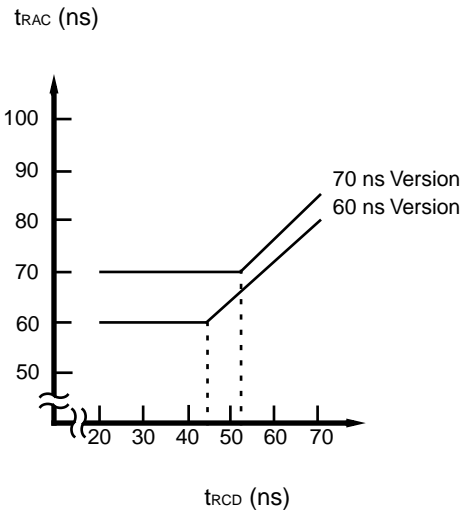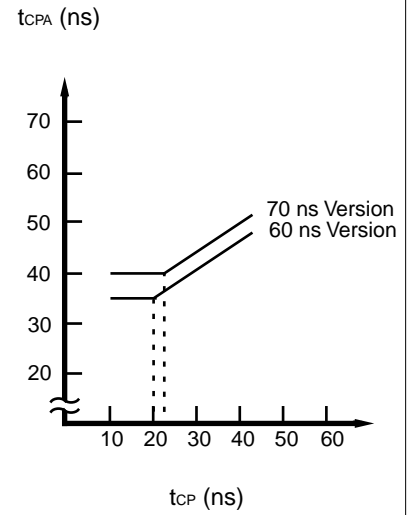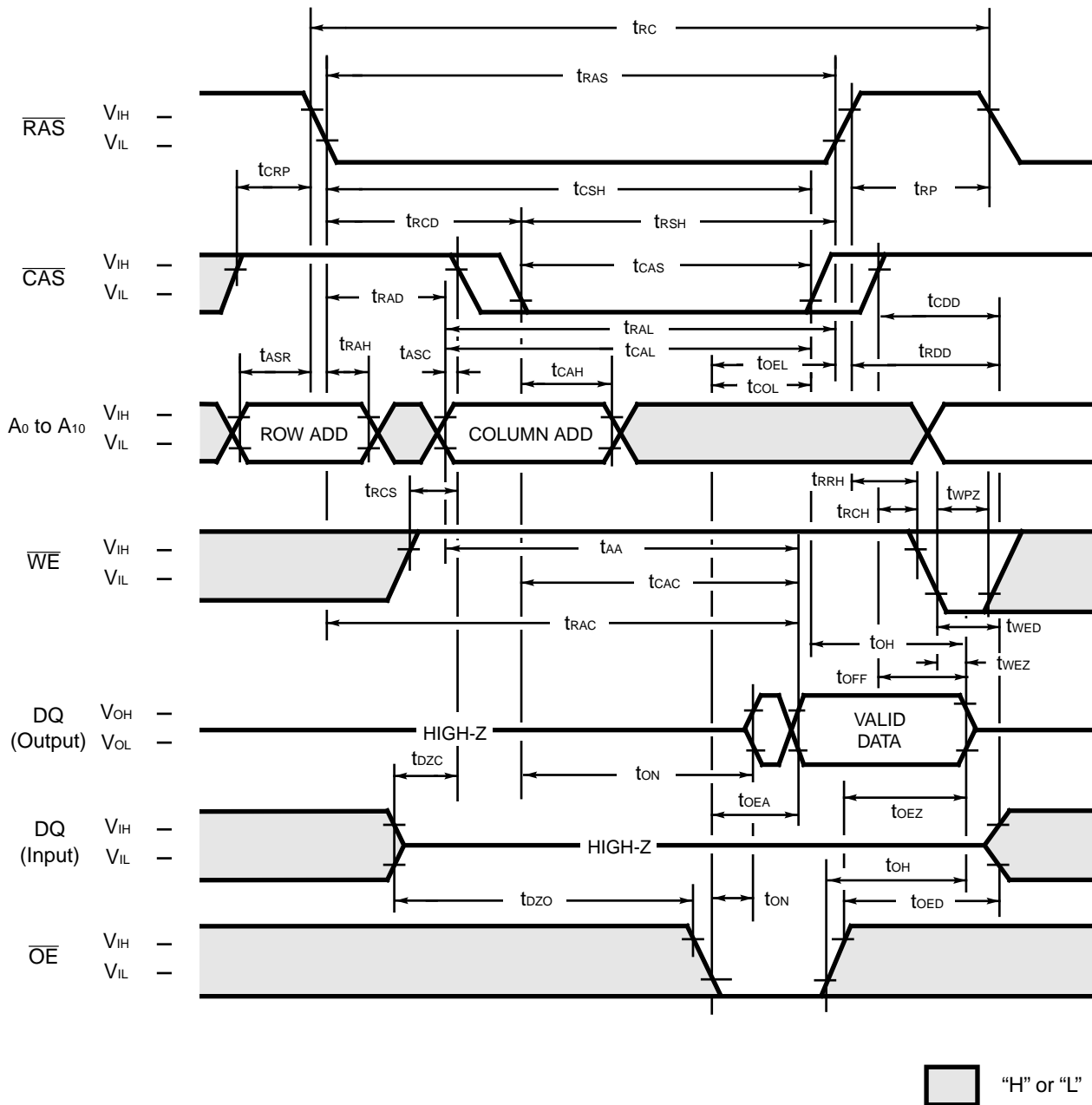
Fig. 3 – t_{RAC} vs. t_{RAD}
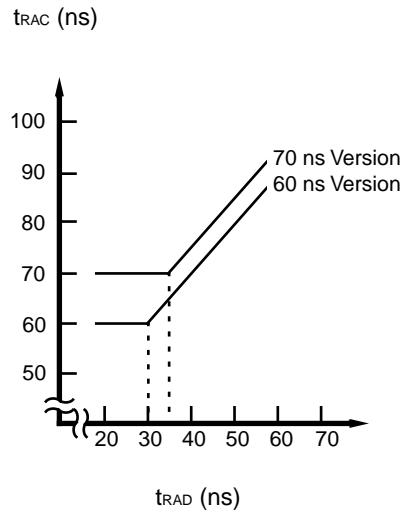
Fig. 4 – t_{CPA} vs. t_{CP}

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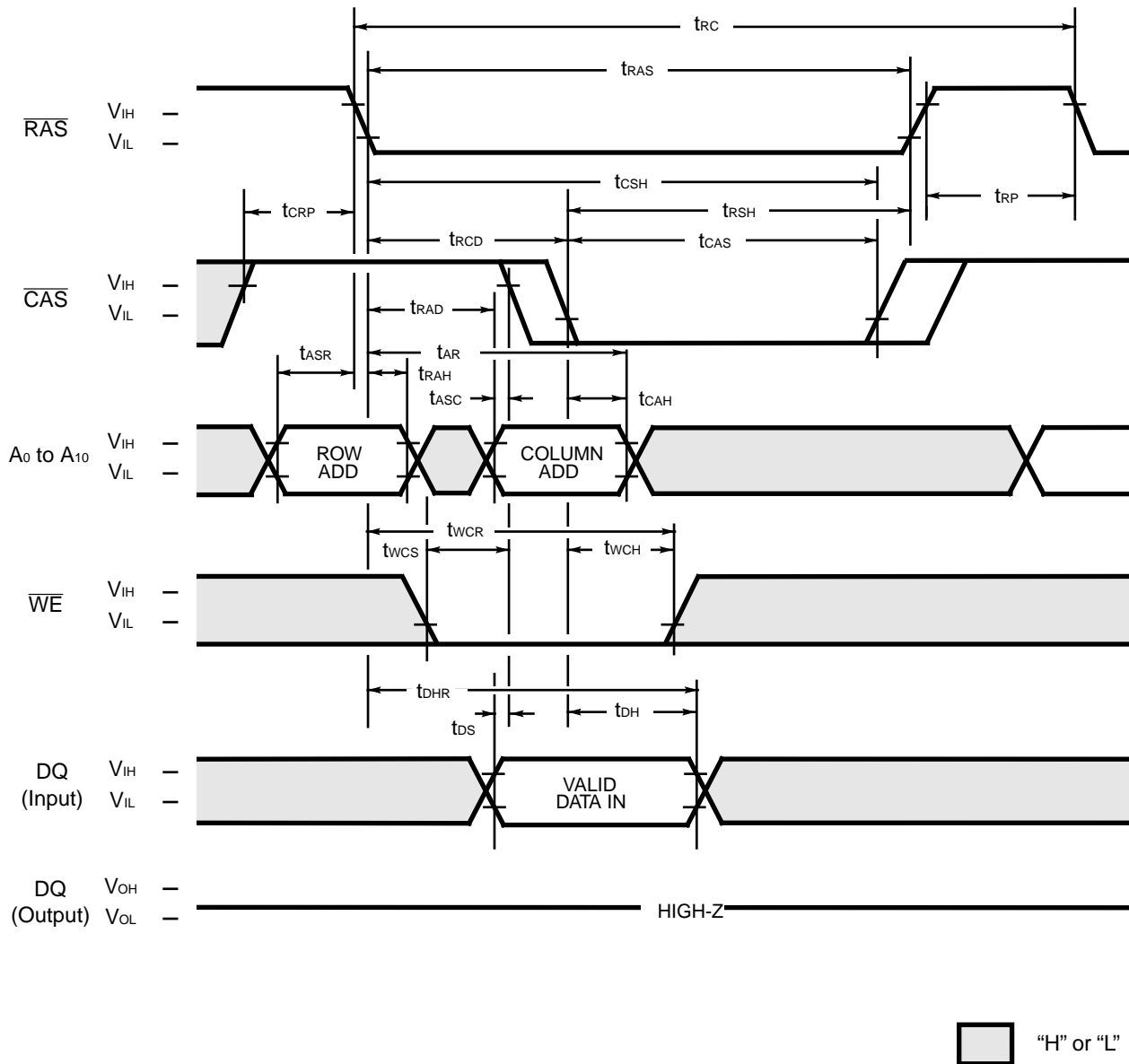

Fig. 4 – READ CYCLE

DESCRIPTION

To implement a read operation, a valid address is latched in by the $\overline{RAS}$ and $\overline{CAS}$ and with $\overline{WE}$ set to a High level and $\overline{OE}$ set to a Low level, the output is valid once the memory access time has elapsed. The access time is determined by $\overline{RAS}$ (t_{RAC}), $\overline{CAS}$ (t_{CAC}), $\overline{OE}$ (t_{OEA}) or column addresses (t_{AA}) under the following conditions:

If $t_{RCD} > t_{RCD}$ (max), access time = t_{CAC}.
If $t_{RAD} > t_{RAD}$ (max), access time = t_{AA}.
If $\overline{OE}$ is brought Low after t_{RAC}, t_{CAC}, or t_{AA} (whichever occurs later), access time = t_{OEA}.

However, if either $\overline{CAS}$ or $\overline{OE}$ goes High, the output returns to a high-impedance state after t_{OH} is satisfied.

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Fig. 5 – EARLY WRITE CYCLE ($\overline{OE}$ = "H" or "L")

DESCRIPTION

A write cycle is similar to a read cycle except $\overline{WE}$ is set to a Low state and $\overline{OE}$ is a "H" or "L" signal. A write cycle can be implemented in either of three ways – early write, $\overline{OE}$ write (delayed write), or read-modify-write. During all write cycles, timing parameters t_{RWL}, t_{CWL} and t_{RAL} must be satisfied. In the early write cycle shown above t_{WCS} satisfied, data on the DQ pin is latched with the falling edge of $\overline{CAS}$ and written into memory.

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Fig. 6 – $\overline{OE}$ (DELAYED WRITE CYCLE)

"H" or "L"

Invalid Data
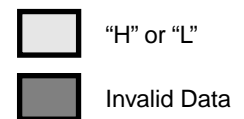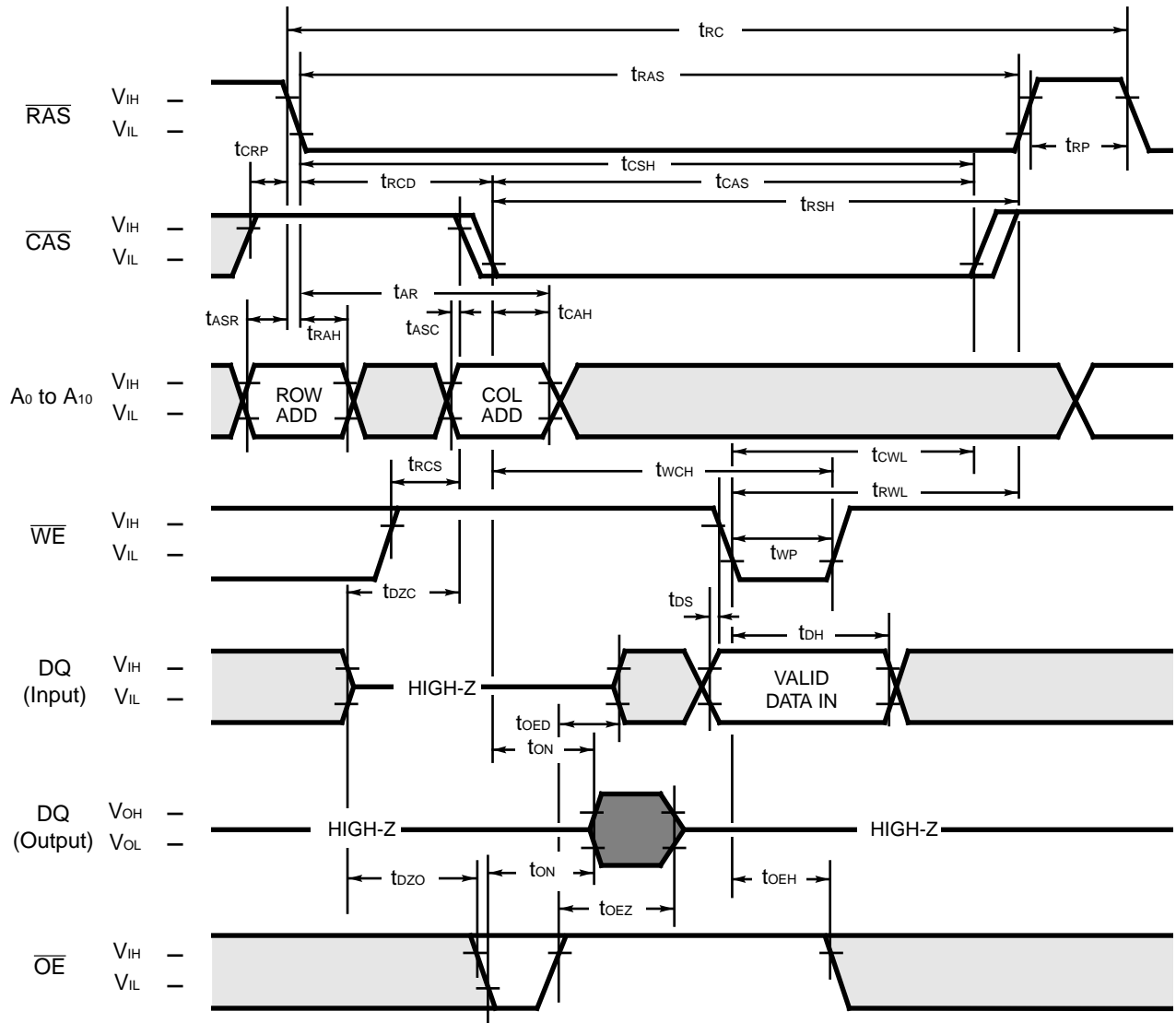
DESCRIPTION

In the $\overline{OE}$ (delayed write) cycle, t_{WCS} is not satisfied; thus, the data on the DQ pins is latched with the falling edge of $\overline{WE}$ and written into memory. The Output Enable ($\overline{OE}$) signal must be changed from Low to High before $\overline{WE}$ goes Low ($t_{OED} + t_{DS}$).

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Fig. 7 – READ-WRITE/READ-MODIFY-WRITE CYCLE

DESCRIPTION

The read-modify-write cycle is executed by changing $\overline{WE}$ from High to Low after the data appears on the DQ pins. In the read-modify-write cycle, $\overline{OE}$ must be changed from Low to High after the memory access time.

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Fig. 8 – HYPER PAGE MODE READ CYCLE

During one cycle is achieved in hyper page mode, the input/output timing apply the same manner as the former cycle.

"H" or "L"

DESCRIPTION

The hyper page mode of operation permits faster successive memory operations at multiple column locations of the same row address.

This operation is performed by strobing in the row address and maintaining $\overline{RAS}$ at a Low level during all successive memory cycles in which the row address is latched. The access time is determined by t_{CAC}, t_{AA}, t_{CPA}, or t_{OEA}, whichever one is the latest in occurring.

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Fig. 9 – HYPER PAGE MODE READ CYCLE ($\overline{OE}$ Control)

During one cycle is achieved in hyper-page mode, the input/output timing apply the same manner as the former cycle.
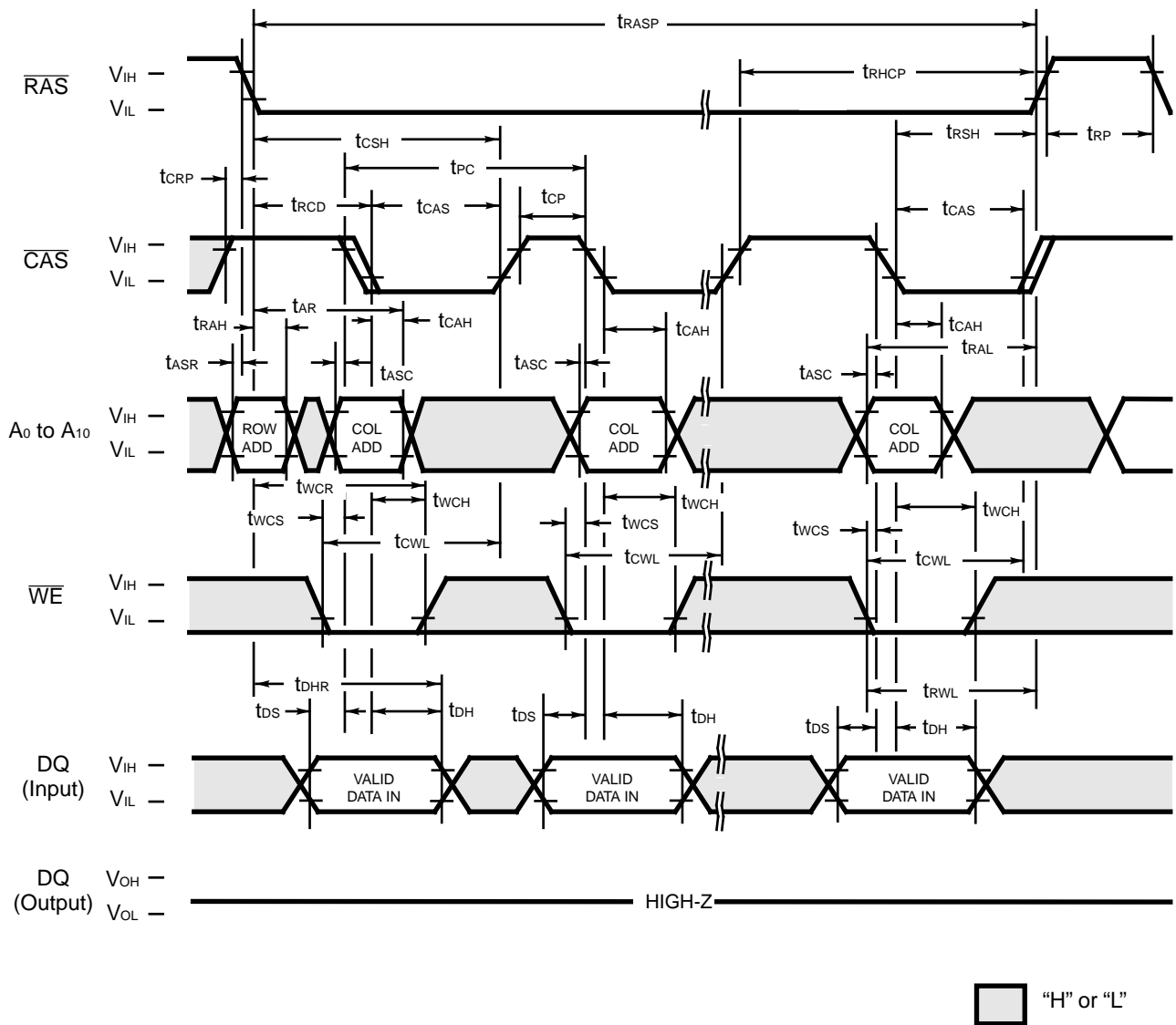
☐ "H" or "L"

■ Valid Data

DESCRIPTION

The hyper page mode of operation permits faster successive memory operations at multiple column locations of the same row address.

This operation is performed by strobing in the row address and maintaining $\overline{RAS}$ at a Low level and $\overline{WE}$ at a High level during all successive memory cycles in which the row address is latched. The access time is determined by t_{CAC}, t_{AA}, t_{CPA}, or t_{OEA}, whichever one is the latest in occurring.

To obtain a high-impedance state, set $\overline{OE}$ or both $\overline{RAS}$ and $\overline{CAS}$ going high level.

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Fig. 10 – HYPER PAGE MODE READ CYCLE ($\overline{WE}$ Control)

During one cycle is achieved in hyper-page mode, the input/output timing apply the same manner as the former cycle.

☐ "H" or "L"

DESCRIPTION

The hyper page mode of operation permits faster successive memory operations at multiple column locations of the same row address. This operation is performed by strobing in the row address and maintaining $\overline{RAS}$ at a Low level during all successive memory cycles in which the row address is latched. The access time is determined by t_{CAC}, t_{AA}, $t_{CPA}$, or t_{OEA}, whichever one is the latest in occurring. To obtain a high-impedance state, confirm either of the following conditions, $\overline{OE}$ set to a High level or $\overline{WE}$ set to a Low level after $\overline{CAS}$ set to a High level or $\overline{RAS}$ and $\overline{CAS}$ set to a High level.

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Fig. 11 – HYPER PAGE MODE EARLY WRITE CYCLE

☐ "H" or "L"

DESCRIPTION

The hyper page mode write cycle is executed in the same manner as the hyper page mode read cycle except the states of $\overline{WE}$ and $\overline{OE}$ are reversed. Data appearing on the DQ pins is latched on the falling edge of $\overline{CAS}$ and written into memory. During the hyper page mode write cycle, including the delayed ($\overline{OE}$) write and read-modify-write cycles, t_{CWL} must be satisfied.

MB81V17405A-60/-70
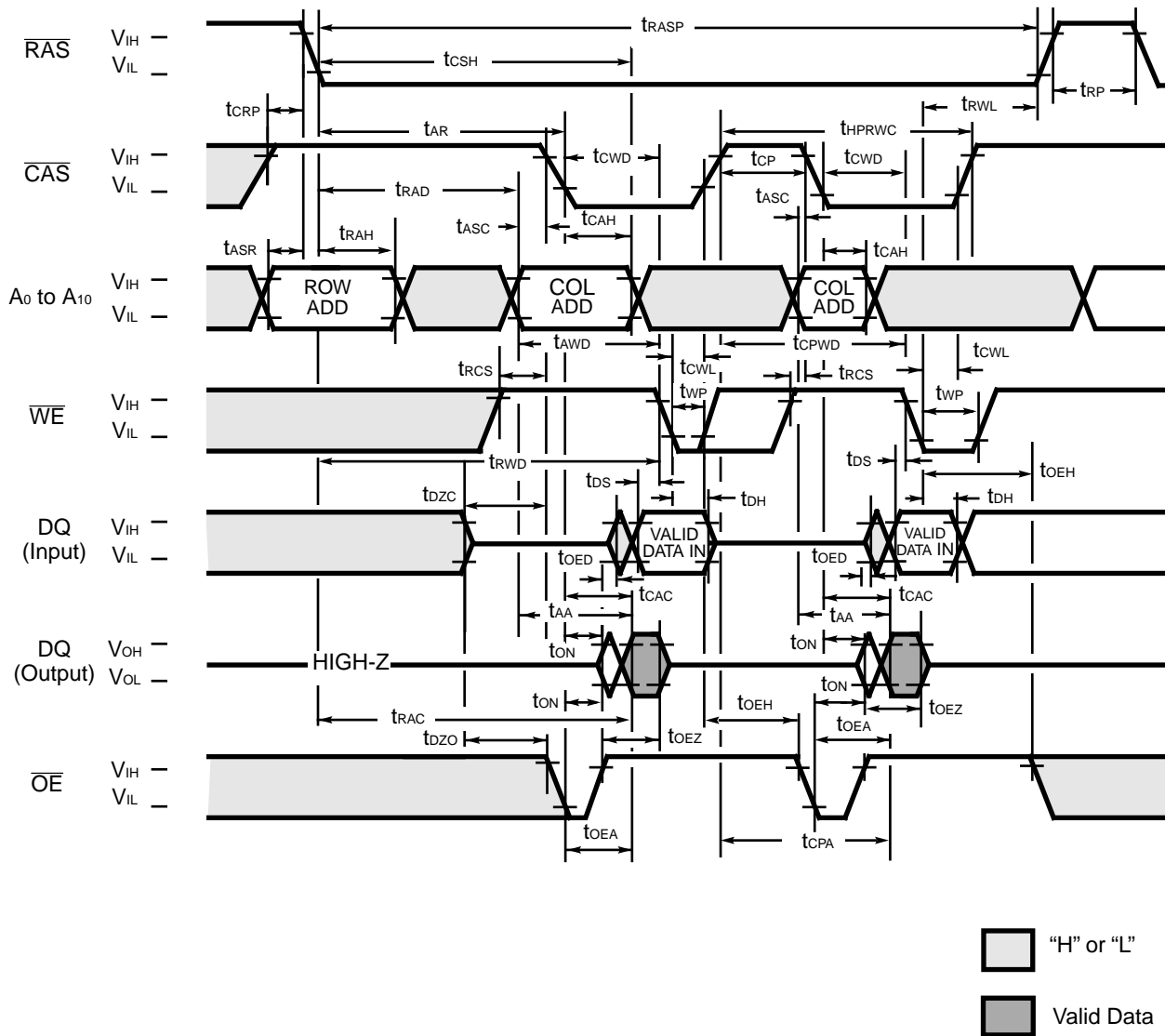
Fig. 12 – HYPER PAGE MODE DELAYED WRITE CYCLE
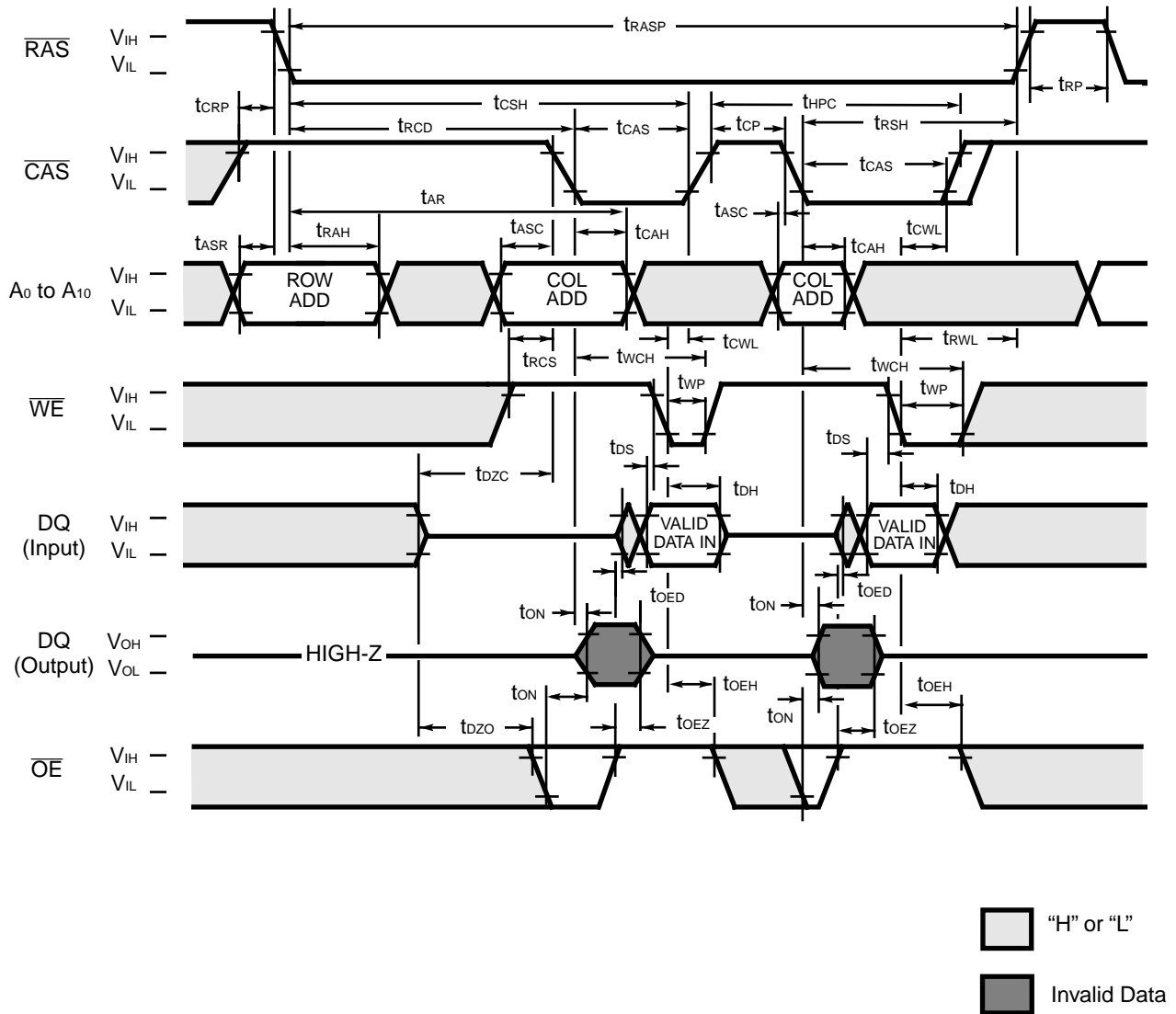
DESCRIPTION

The hyper page mode delayed write cycle is executed in the same manner as the hyper page mode early write cycle except for the states of $\overline{WE}$ and $\overline{OE}$. Input data on the DQ pins are latched on the falling edge of $\overline{WE}$ and written into memory. In the hyper page mode delayed write cycle, $\overline{OE}$ must be changed from Low to High before $\overline{WE}$ goes Low ($t_{OED} + t_T + t_{DS}$).

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Fig. 13 – HYPER PAGE MODE READ/WRITE CYCLE

☐ "H" or "L"

DESCRIPTION

The hyper page mode performs read/write operations repetitively during one $\overline{RAS}$ cycle. At this time, t_{HPC} (min) is invalid.

MB81V17405A-60/-70
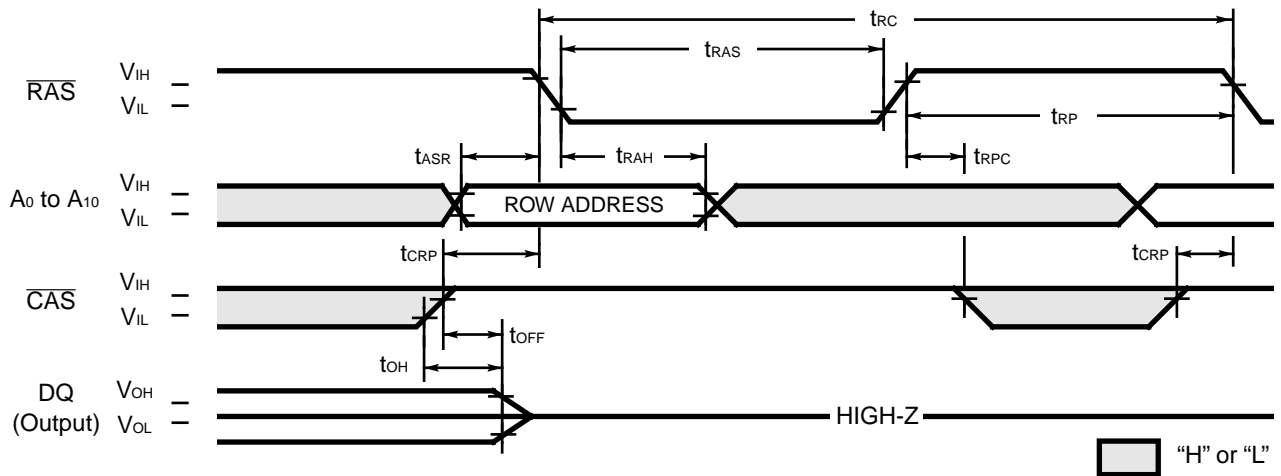
Fig. 14 – HYPER PAGE MODE READ-MODIFY-WRITE CYCLE

DESCRIPTION

During the hyper page mode of operation, the read-modify-write cycle can be executed by switching $\overline{WE}$ from High to Low after input data appears at the DQ pins during a normal cycle.

Fig. 15 – $\overline{RAS}$-ONLY REFRESH ($\overline{WE} = \overline{OE}$ = "H" or "L")

DESCRIPTION

Refresh of RAM memory cells is accomplished by performing a read, a write, or a read-modify-write cycle at each of 2048 row addresses every 32.8-milliseconds. Three refresh modes are available: $\overline{RAS}$-only refresh, $\overline{CAS}$-before-$\overline{RAS}$ refresh, and hidden refresh.

$\overline{RAS}$-only refresh is performed by keeping $\overline{RAS}$ Low and $\overline{CAS}$ High throughout the cycle; the row address to be refreshed is latched on the falling edge of $\overline{RAS}$. During $\overline{RAS}$-only refresh, D_{OUT} pin is kept in a high-impedance state.

Fig. 16 – $\overline{CAS}$-BEFORE-$\overline{RAS}$ REFRESH (ADDRESSES = $\overline{WE} = \overline{OE}$ = "H" or "L")
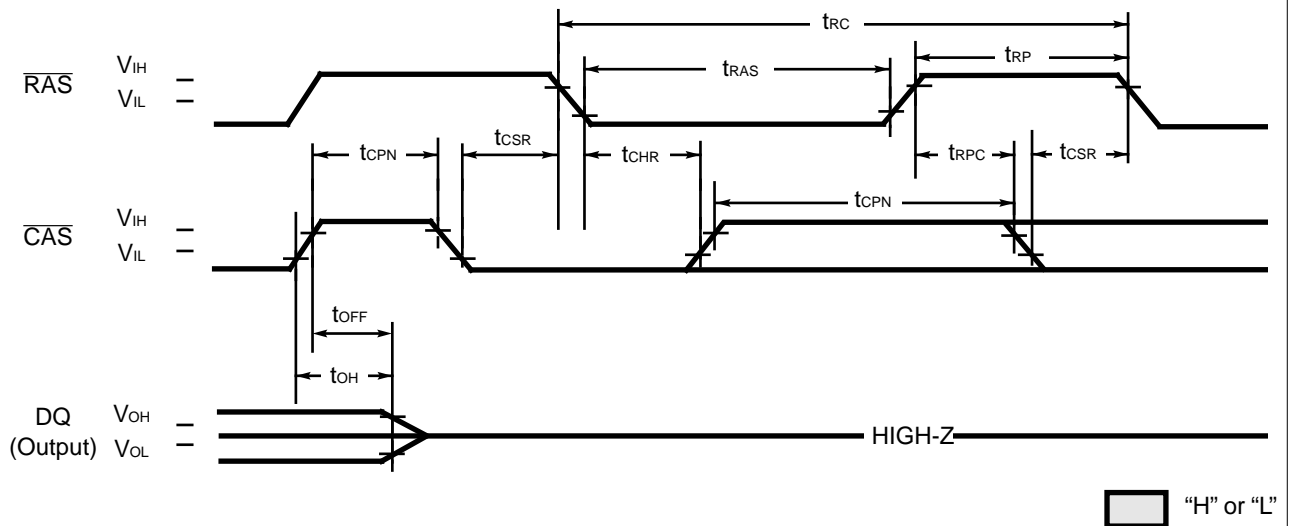
DESCRIPTION

$\overline{CAS}$-before-$\overline{RAS}$ refresh is an on-chip refresh capability that eliminates the need for external refresh addresses. If $\overline{CAS}$ is held Low for the specified setup time (t_{CSR}) before $\overline{RAS}$ goes Low, the on-chip refresh control clock generators and refresh address counter are enabled. An internal refresh operation automatically occurs and the refresh address counter is internally incremented in preparation for the next $\overline{CAS}$-before-$\overline{RAS}$ refresh operation.
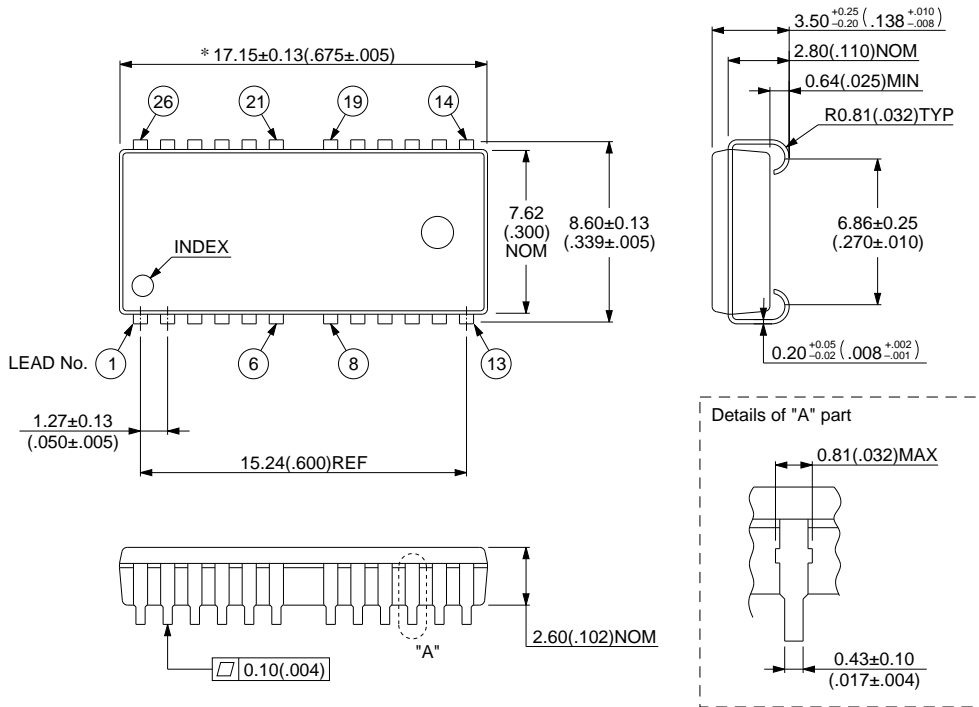
25

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Fig. 17 – HIDDEN REFRESH CYCLE

DESCRIPTION

A hidden refresh cycle may be performed while maintaining the latest valid data at the output by extending the active time of $\overline{CAS}$ and cycling $\overline{RAS}$. The refresh row address is provided by the on-chip refresh address counter. This eliminates the need for the external row address that is required by DRAMs that do not have $\overline{CAS}$-before-$\overline{RAS}$ refresh capability.

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Fig. 18 – $\overline{CAS}$-BEFORE-$\overline{RAS}$ REFRESH COUNTER TEST CYCLE

"H" or "L"

Valid Data

DESCRIPTION

A special timing sequence using the $\overline{CAS}$-before-$\overline{RAS}$ refresh counter test cycle provides a convenient method to verify the functionality of $\overline{CAS}$-before-$\overline{RAS}$ refresh circuitry. If, after a $\overline{CAS}$-before-$\overline{RAS}$ refresh cycle $\overline{CAS}$ makes a transition from High to Low while $\overline{RAS}$ is held Low, read and write operations are enabled as shown above. Row and column addresses are defined as follows:

Row Address: Bits A_0 through A_{10} are defined by the on-chip refresh counter.
Column Address: Bits A_0 through A_{10} are defined by latching levels on A_0 to A_{10} at the second falling edge of $\overline{CAS}$.

The $\overline{CAS}$-before-$\overline{RAS}$ Counter Test procedure is as follows ;

1) Initialize the internal refresh address counter by using 8 $\overline{RAS}$-only refresh cycles.
2) Use the same column address throughout the test.
3) Write "0" to all 2048 row addresses at the same column address by using normal write cycles.
4) Read "0" written in procedure 3) and check; simultaneously write "1" to the same addresses by using $\overline{CAS}$-before-$\overline{RAS}$ refresh counter test (read-modify-write cycles). Repeat this procedure 2048 times with addresses generated by the internal refresh address counter.
5) Read and check data written in procedure 4) by using normal read cycle for all 2048 memory locations.
6) Reverse test data and repeat procedures 3), 4), and 5).

(At recommended operating conditions unless otherwise noted.)

No.	Parameter	Symbol	MB81V17405A-60		MB81V17405A-70		Unit
			Min.	Max.	Min.	Max.	
69	Access Time for $\overline{CAS}$	t_{FCAC}	—	50	—	55	ns
70	Column Address Hold Time	t_{FCAH}	35	—	35	—	ns
71	$\overline{CAS}$ to $\overline{WE}$ Delay Time	t_{FCWD}	70	—	77	—	ns
72	$\overline{CAS}$ Pulse Width	t_{FCAS}	90	—	99	—	ns
73	$\overline{RAS}$ Hold Time	t_{FRSH}	90	—	99	—	ns

Note: Assumes that $\overline{CAS}$-before-$\overline{RAS}$ refresh counter test cycle only.

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■ PACKAGE DIMENSIONS

26-LEAD PLASTIC LEADED CHIP CARRIER

*: This dimension excludes resin protrusion. (Each side: .006 (0.15) MAX)
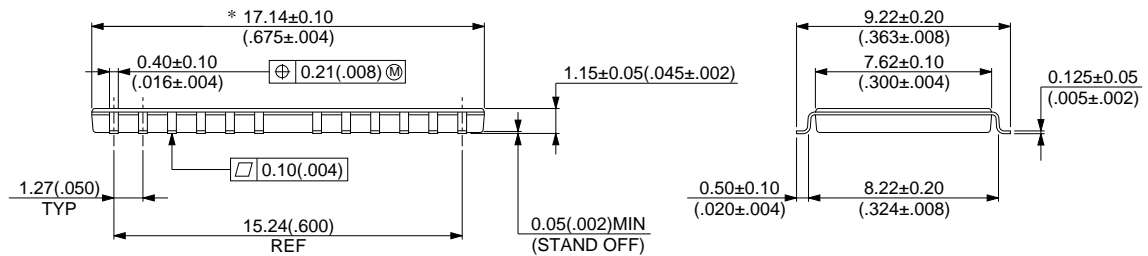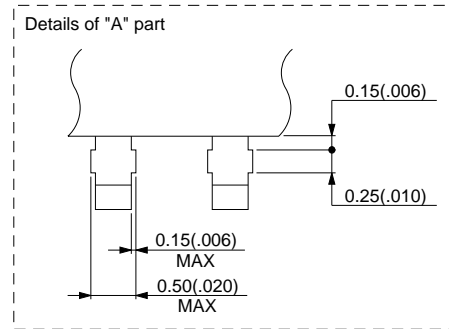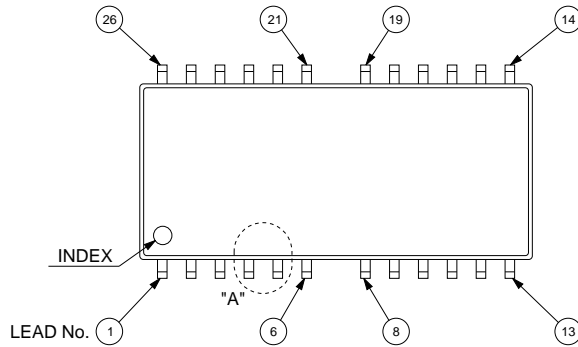

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Dimensions in mm (inches)

28

MB81V17405A-60/-70

■ PACKAGE DIMENSIONS

26-LEAD PLASTIC FLAT PACKAGE

*: This dimension excludes resin protrusion. (Each side: .006 (0.15) MAX)

Details of "A" part

0.15(.006)

0.25(.010)

0.15(.006)
MAX

0.50(.020)
MAX

INDEX

"A"

LEAD No. ①   ⑥   ⑧   ⑬

㉖   ㉑   ⑲   ⑭

* 17.14±0.10
(.675±.004)

0.40±0.10
(.016±.004)   ⊕ 0.21(.008) Ⓜ

1.15±0.05(.045±.002)

□ 0.10(.004)

1.27(.050)
TYP

15.24(.600)
REF

0.05(.002)MIN
(STAND OFF)

9.22±0.20
(.363±.008)

7.62±0.10
(.300±.004)

0.125±0.05
(.005±.002)

0.50±0.10
(.020±.004)

8.22±0.20
(.324±.008)

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Dimensions in mm (inches)

MB81V17405A-60/-70

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